

PVT

CFD

LG

CFD Simulation of Rarefied Gas Flows in Physical Vapor Transport (PVT)

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Physical Vapor Transport (PVT) is a process used for the purification of materials. It involves the evaporation of a material from a source and its subsequent condensation on a target. This process is often used in the semiconductor industry for the deposition of thin films. The PVT process can be performed in either a closed or an open ampoule. The choice between closed and open ampoules depends on the material being processed and the desired purity. In a closed ampoule, the material is contained within a sealed container, which prevents contamination from the environment. However, this setup can be more complex and expensive. In an open ampoule, the material is exposed to the atmosphere, which can lead to contamination but is generally simpler and less expensive. The PVT process is also used in microgravity environments, where the absence of gravity allows for more uniform deposition of materials. This is particularly useful for the production of high-quality thin films and coatings. The simulation of PVT processes using Computational Fluid Dynamics (CFD) is a challenging task due to the rarefied nature of the gas flows involved. CFD models for PVT must account for non-continuum effects, such as slip and jump boundary conditions (SJBCs), which are not captured by standard Navier-Stokes equations. The simulation of PVT processes using CFD is often performed using software packages like FLUENT 6. The simulation results can provide valuable insights into the PVT process, such as the distribution of the material and the rate of deposition. The simulation of PVT processes using CFD is a rapidly growing field, and it is expected to continue to play an important role in the development of new materials and processes.

1 PVT 가
 가 source zone , PVT
 (mean free path)

PVT Kn 0.1 , Navier-Stokes SJBCs
 [3]. Thermal creep 1 SJBCs

$$\mathbf{v} - \mathbf{v}_w = \frac{2 - \sigma_v}{\sigma_v} \lambda \left(\frac{\partial \mathbf{v}}{\partial n} \right) \quad (1)$$

$$T - T_w = \frac{2 - \sigma_T}{\sigma_T} \left[\frac{2\gamma}{(\gamma + 1)} \right] \frac{\lambda}{Pr} \left(\frac{\partial T}{\partial n} \right) \quad (2)$$

λ = mean free path, σ_v = tangential-momentum-accommodation coefficient, σ_T = thermal accommodation coefficient, γ = specific heat ratio, Pr = Prandtl number, w
 가 가

PVT
 convection roll convection roll
 가 [1,2], PVT

Gr Reynolds (Re) 가
 Boussinesq 가 Navier-Stokes
 2 (,) ()
 2(a), 가 2(b),
 (2(c)). 가
 가 Gr/Re²
 가

가 3 가 3 가

— PVT , FLUENT

CFD 3

1. Mackowski, D.W., Rao, V.R., Walker, D.G., and Knight, R.W., “Numerical Investigation of the Effects of Thermal Creep in Physical Vapor Transport”, *J. Crystal Growth*, **179**, 297 (1997)
2. Fujiwara, S., Watanabe, Y., Namikawa, Y., Keishi, T., Matsumoto, K., and Kotani, T., “Numerical Simulation on Dumping of Convection by Rotating a Horizontal Cylinder during Crystal Growth from Vapor”, *J. Crystal Growth*, **192**, 328 (1998)
3. Gad-el-Hak, M., “Flow Physics in MEMS”, *Mec. Ind.*, **2**, 313 (2001)

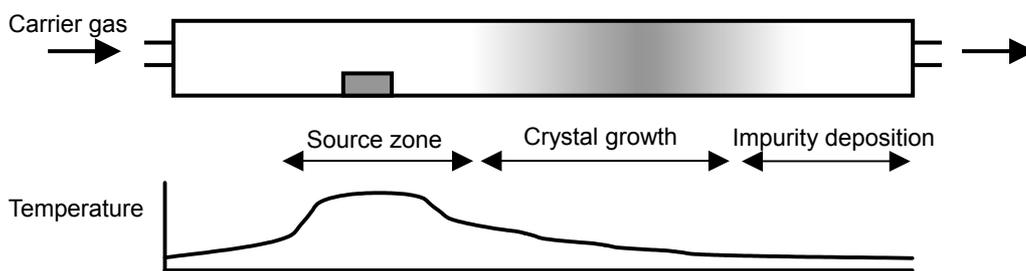


Figure 1: Crystal growth process using PVT

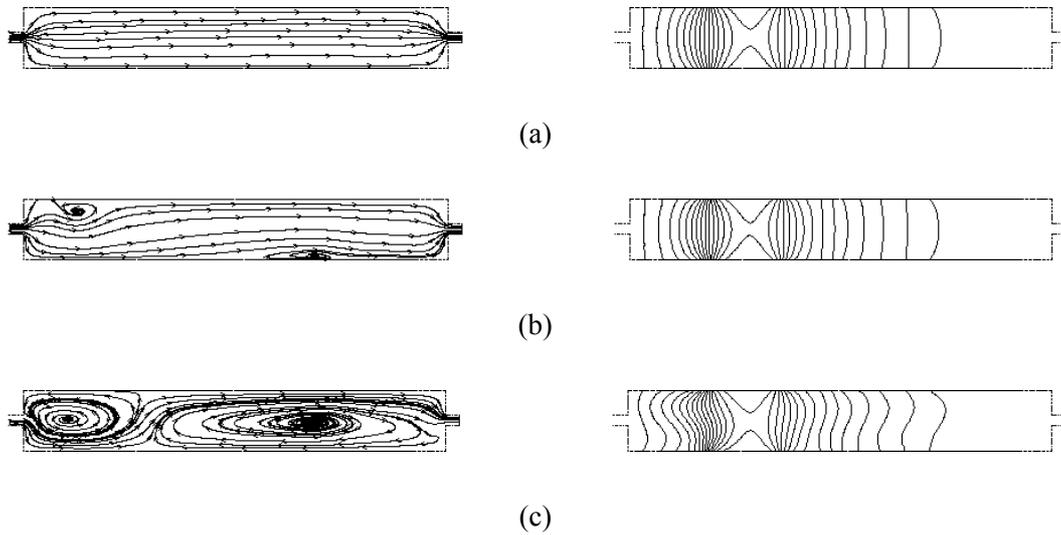


Figure 2: Streamlines (left) and temperature contours (right): dimensionless tube radius =1, dimensionless pressure at outlet = (a) 0.0247, (b) 1.00, and (c) 48.4

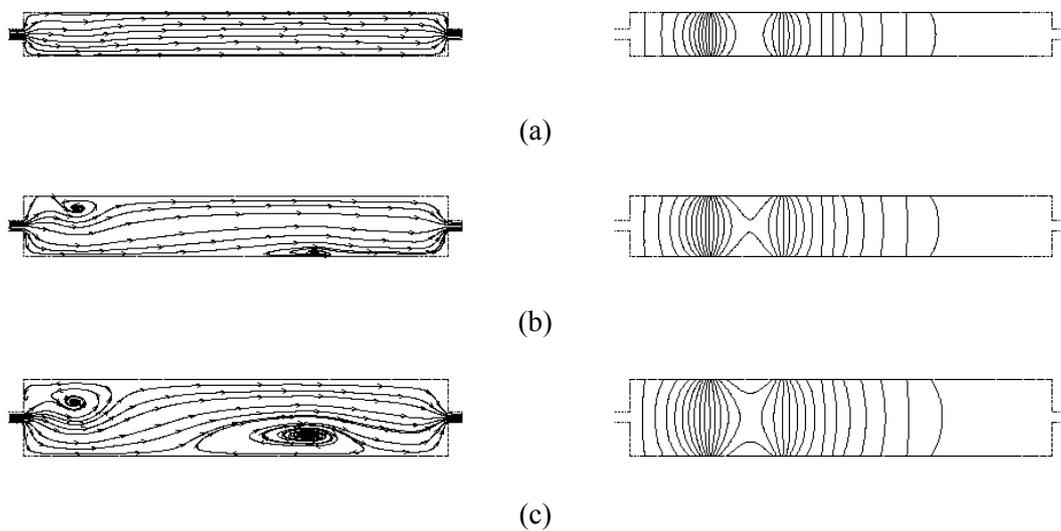


Figure 3: Streamlines (left) and temperature contours (right): dimensionless pressure at outlet = 1, dimensionless tube radius = (a) 0.714, (b) 1.00, and (c) 1.286